

Conduct
Q1
performing a wet clean step in the presence of the conditioned silicon oxynitride layer, wherein the wet clean step cleans the trench in the semiconductor substrate.

Q2
13. (Amended) The method of Claim 12, further comprising etching the silicon oxynitride layer, the silicon nitride layer, the pad oxide and the semiconductor substrate through the photoresist mask, thereby forming the trench in the semiconductor substrate.
